Bias Stabilization :-

Only the fixing of a suitable operating point is not sufficient but it is also to be ensured that the operating point remains stable. i.e. it does not shift due to change in temperature or due to variations in translator parameters (due to replacement of translator). It is not possible in practice unless special efforts are made to achieveit. The maintenance of the operating point stable is known as stabilization.

The stabilization of operating point is essential because of (i) temperature dependance of Callector current Ic (ii) individual variations and viii) thermal runaway.

Stability factor!

The degree of success achieved in stability factor is expressed in terms of stability factor 'S' and it is defined as the rate of change of collector current court. Ico keeping B and VBE Constant

 $S = \frac{\partial I_c}{\partial I_{co}} |_{ad \ constant \ \beta \ and \ VBE (or IB)}$

General Expression for Stability Factor:

Partial Differentiation wort. In

$$I = \beta \frac{\partial IB}{\partial I_c} + (I+\beta) \frac{\partial I_{co}}{\partial I_c}$$

$$\frac{\partial I_{co}}{\partial I_{c}} = \frac{1 - \beta \left(\frac{\partial I_{B}}{\partial I_{c}}\right)}{\left(1 + \beta\right)}$$

$$\frac{\partial I_c}{\partial k_0} = \frac{1 + \beta}{1 - \beta \left(\frac{\partial I_B}{\partial I_c}\right)}$$

Transistor Biasing Circuits :-

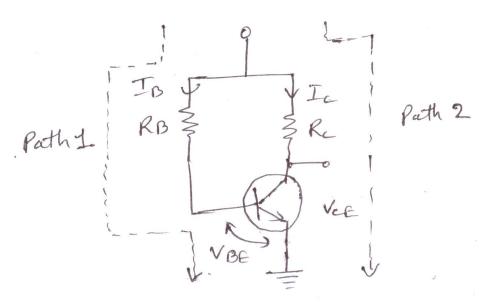
associated with a transistor should fulfill the following requirements

cir Estabilish the operating point in the middle of the active region of the characteristics, so that on applying the input signal the instantaneous operating point does not move either to the cut off region or to the saturation region, even at the extreme values of the input signal.

(ii) Stabilize the collector current Ic against temperature variations.

(iii) Make the operating point independent of transistor parameters so that replacement of transistor by another of the same type in the circuit does not shift the operating point.

(i) fixed Bias Circuit:



The base current can be determined by applying kirchhoff's voltage law on path 1.

$$V_{cc} = I_{B}R_{B} + V_{BE}$$

$$I_{B} = \frac{V_{cc} - V_{BE}}{R_{B}}$$

$$I_{c} = \beta I_{B}$$

For Si Transissor VBE = 0.7 For Ge VBE = 0.3

Porth - 2

we know that

$$S = \frac{1 + \beta}{1 - \beta \left(\frac{\partial I_{\beta}}{\partial I_{\epsilon}}\right)}$$

This value of s is very high and for stability.
This should be minimum.

Les

It desires its name from The fact that voltage path (丁の十三) for RB is derived from the ID RB Collector. There exists a negative feedback effect which tends to stabilise VBE Ic against changes either as a result of change in temperature or as a result of replacement of the transistor. If the collector current Ic tends to increase, & Ver decreases due to larger veltage drop across The collector resistance Re. The result is that base current Is is reduced. The reduced base current in turn reduces the original increase in Collector current Ic. Thus a mechanism exists in the circuit which does not allow callector current Ie to increase supidly.

Path (1) KVL

Vcc = (Ic+IB) Re+ IBRB + VBE = (PIB+IB) Rc+ IBRB+ VBE

and Ver we can also write.

(8) 98°

$$S = \frac{1+100}{1+100(10)} = \frac{101}{11}$$

for the same value of (5=100) the stability of Collector to Base. Blase is more than fixed biase.

Potential Divider Blas 3o Vee or Voltage Divider Bias] or self Bias. This is the most commonly Used biaring arrangement. The name potential divider is derived due to the fact that The voltage devider is formed by the revisions R, and R2 acress Nec. The omitter revision RE provides stabilization. The revisitor RE causes a voldage drop in a direction to so as to reverte biase. The emitter junction. Since the emitter-base junction is to to forward biased, the base voltage is obtained from supply Vec through RI-R. network. is shown in Therenin's equivalent circuit of fig 1. fig. 2. som the ckt. Rth = RIIIR2 = RIK2
RTR2 Non = R2 Vec

Bare loop

KVL in Base loop.

Stabilizing Factor

$$\frac{\partial I_B}{\partial I_C} = -\frac{R_E}{R_{th} + R_E} \left[\frac{S}{S} = \frac{1 + \beta}{1 + \beta \left(\frac{R_E}{R_{th} + R_E} \right)} \right]$$